

5

UTILITY APPLICATION

BY

10

FREDRICK A. PERNER
AND
MANOJ BHATTACHARYYA

15

FOR

UNITED STATES PATENT

ON

20

CONTROLLED TEMPERATURE, THERMAL-ASSISTED MAGNETIC MEMORY
DEVICE

25

Docket No: 200310251-1
Sheets of Drawings: Five (5)
Express Mail No.: **EL 993396569 US**

30

HEWLETT-PACKARD COMPANY
Intellectual Property Administration
P.O. Box 272400
Fort Collins, Colorado 80527-2400

35

Attorneys
Brian Short
Daniel W. Roberts

CONTROLLED TEMPERATURE, THERMAL-ASSISTED MAGNETIC MEMORY DEVICE

FIELD OF THE INVENTION

5 **[0001]** This invention relates generally to magnetic memory devices, and in particular to ultra-high density thermally assisted magnetic random access memory arrays (commonly referred to as "MRAM").

BACKGROUND OF THE INVENTION

10 **[0002]** Today's computer systems are becoming increasingly sophisticated, permitting users to perform an ever greater variety of computing tasks at faster and faster rates. The size of the memory and the speed at which it can be accessed bear heavily upon the overall speed of the computer system.

15 **[0003]** Memory for a computer system is technically any form of electronic, magnetic or optical storage; however, it is generally divided up into different categories based in part upon speed and functionality. The two general categories of computer memory are main memory and mass storage. Main memory is generally comprised of fast, expensive volatile random access memory that is connected directly to the processor by a memory bus. One contributor to the speed in main memory is generally the ability to access a particular
20 memory cell without physical movement of components.

25 **[0004]** Generally, the principle underlying the storage of data in magnetic media (main or mass storage) is the ability to change and/or reverse the relative orientation of the magnetization of a storage data bit (i.e. the logic state of a "0" or a "1"). The coercivity of a material is the level of demagnetizing force that must be applied to a magnetic particle to reduce and/or reverse the magnetization of the particle.

30 **[0005]** A prior art magnetic memory cell may be a tunneling magneto-resistance memory cell (TMR), a giant magneto-resistance memory cell (GMR), or a colossal magneto-resistance memory cell (CMR). These types of magnetic memory are commonly referred to as spin valve memory cells (SVM). FIGS. 1A and 1B provide a perspective view of a typical prior art magnetic memory cell having two conductors.

30 **[0006]** As shown in prior art FIG. 1A and 1B, a magnetic spin valve memory cell **100** generally includes a data layer **101** (also called a storage layer or bit layer), a reference layer **103**, and an intermediate layer **105** between the data layer **101** and the reference layer **103**. The data layer **101**, the reference layer **103**, and the intermediate layer **105** can be made

from one or more layers of material. Electrical current and magnetic fields may be provided to the SVM cell **100** by an electrically conductive row conductor **107** and an electrically conductive column conductor **109**.

[0007] In a typical MRAM device, the SVM cells are arranged in a cross-point array. Parallel conductive columns (column 1, 2, 3...), also referred to as word lines, cross parallel conductive rows (row A, B, C...), also referred to as bit lines. The traditional principles of column and row arrays dictate that any given row will only cross any given column once.

[0008] An SVM cell is placed at each intersecting cross-point between a row and column. By selecting a particular row (B) and a particular column (3), any one memory cell positioned at their intersection (B,3) can be isolated from any other memory cell in the array. Such individual indexing is not without complexities. A typical MRAM cross-point array may easily consist of at least 1,000 rows and 1,000 columns uniquely addressing 1,000,000 SVM cells.

[0009] The data layer **101** is usually a layer of magnetic material that stores a bit of data as an orientation of magnetization M2 that may be altered in response to the application of an external magnetic field or fields. More specifically, the orientation of magnetization M2 of the data layer **101** representing the logic state can be rotated (switched) from a first orientation, representing a logic state of "0", to a second orientation, representing a logic state of "1", and/or vice versa.

[0010] The reference layer **103** is usually a layer of magnetic material in which an orientation of magnetization M1 is "pinned", as in fixed, in a predetermined direction. The direction is predetermined and established by microelectronic processing steps employed in the fabrication of the magnetic memory cell.

[0011] Typically, the logic state (a "0" or a "1") of a magnetic memory cell depends on the relative orientations of magnetization in the data layer **101** and the reference layer **103**. For example, when an electrical potential bias is applied across the data layer **101** and the reference layer **103** in an SVM cell **100**, electrons migrate between the data layer **101** and the reference layer **103** through the intermediate layer **105**. The intermediate layer **105** is typically a thin dielectric layer commonly referred to as a tunnel barrier layer. The phenomena that cause the migration of electrons through the barrier layer may be referred to as quantum mechanical tunneling, or spin tunneling.

[0012] The logic state may be determined by measuring the resistance of the memory cell. For example, if the overall orientation of the magnetization in the data layer **101** is parallel to the pinned orientation of magnetization in the reference layer **103** the magnetic memory cell will be in a state of low resistance, R.

5 **[0013]** If the overall orientation of the magnetization in the data layer **101** is anti-parallel (opposite) to the pinned orientation of magnetization in the reference layer **103**, the magnetic memory cell will be in a state of high resistance $R + \Delta R$. The orientation of M2 and, therefore, the logic state of the SVM cell **100** may be read by sensing the resistance of the SVM cell **100**.

10 **[0014]** With respect to coercivity, generally speaking, the smaller the magnetic particle, the higher its coercivity. A large coercivity is generally undesirable as it requires a greater magnetic field to facilitate switching, which in turn requires a greater power source and potentially larger conductors. Providing a large power source and large conductors is generally at odds with the attempts to reduce the necessary size of components, and
15 therefore permit larger memory stores in smaller and smaller spaces.

[0015] In addition, the coercivity of a magnetic particle may also be affected by temperature. Generally, as temperature increases, coercivity decreases. With respect to MRAM and SVM cells, elevating the temperature of an SVM cell may indeed reduce the coercivity. In an MRAM array, switching the magnetic orientation of a specific cell without
20 substantially disturbing the others can be facilitated by heating the selected cell, and thus lowering that particular SVM cell's coercivity. Such a heated SVM cell may then be switched by a field that is insufficient to affect unselected neighboring SVM cells.

[0016] However, environmental factors may significantly affect the SVM cell. Heat applied to an SVM cell in one setting to reduce its coercivity may be ineffective in another,
25 i.e., where the cell is extremely cold.

[0017] Likewise, where the ambient temperature is extremely warm, additional heat (and the switching field itself) may inadvertently affect more than the specifically intended SVM cell. The variable of ambient temperature and the effect on the operation of the MRAM can therefore degrade proper operation of the SVM cells.

30 **[0018]** In a typical MRAM array, a significant amount of overall space may be used simply to provide a physical buffer between the cells. Eliminating this buffering space, or reducing its ratio, could provide a greater volume of storage in the same physical space

[0019] Hence, there is a need for an ultra-high density thermally assisted memory array which overcomes one or more of the drawbacks identified above. The present invention satisfies this need.

5

SUMMARY

[0020] This invention provides a controlled temperature, thermal-assisted magnetic memory device for use as an ultra-high density memory array.

10 [0021] In particular, and by way of example only, according to an embodiment of the present invention, this invention provides a controlled temperature, thermal-assisted magnetic memory device including: an array of SVM cells, the SVM cells characterized by an alterable orientation of magnetization and including a material wherein the coercivity is decreased upon an increase in temperature; at least one reference SVM cell; and a feedback controlled temperature controller receiving a reference voltage and receiving feedback a voltage from the reference SVM cell when power is applied to the reference SVM cell and a
15 selected array SVM cell to heat the reference SVM cell and the selected array SVM cell, the feedback controlled temperature controller adjusting the applied power to minimize the difference between the feedback voltage and reference voltage.

[0022] In yet another embodiment, the invention may provide a method of performing a write operation on a selected SVM cell in a controlled temperature, thermal-assisted
20 memory device consisting of an array of SVM cells wherein their coercivity is decreased upon an increase in temperature, a reference SVM cell substantially similar to and in close proximity to the array, and a feedback controlled temperature controller having a temperature sensor thermally coupled to the reference SVM cell, the method including: selecting a specific SVM cell from the array; applying a first power to the reference SVM
25 cell, the first power heating the reference SVM cell; applying a second power, substantially identical to the first power, to the selected SVM cell, the second power heating selected SVM cell; sensing a feedback voltage from the temperature sensor coupled to the reference SVM cell; comparing the feedback voltage to a reference voltage; adjusting the first power applied to the reference SVM cell to minimize the difference between the feedback voltage
30 and the reference voltage; adjusting the second power applied to the selected SVM cell to be substantially identical to the adjusted first voltage; and applying a magnetic field to the selected SVM cell; wherein the orientation of magnetization of the selected array SVM cell may be changed, the magnetic field being greater than the coercivity of the heated selected array SVM cell.

[0023] These and other objects, features and advantages of the preferred method and apparatus will become apparent from the following detailed description, taken in conjunction with the accompanying drawings which illustrate, by way of example, the principles of the invention.

5

BRIEF DESCRIPTION OF THE DRAWINGS

[0024] FIGS. 1A ~1B provide perspective views of a prior art magnetic memory cell;

[0025] FIG. 2 is a block diagram of the controlled temperature, thermal-assisted magnetic memory device according to the present invention;

10 [0026] FIG. 3 is a partial perspective view of a cross-point array and reference SVM cell as shown in FIG. 2;

[0027] FIG. 4 is a conceptual electrical diagram of the controlled temperature, thermal-assisted magnetic memory device shown in FIG. 2;

15 [0028] FIG. 5 is a flowchart depicting the steps of using the controlled temperature, thermal-assisted magnetic memory device as shown in FIGS. 2, 3 and 4.

DETAILED DESCRIPTION

20 [0029] Before proceeding with the detailed description, it is to be appreciated that the present invention is not limited to use or application with a specific type of magnetic memory. Thus, although the present invention is, for the convenience of explanation, depicted and described with respect to typical exemplary embodiments, it will be appreciated that this invention may be applied with other types of magnetic memory.

25 [0030] Referring now to the drawings, and more particularly to FIG. 2, there is shown a portion of a controlled temperature, thermal-assisted magnetic memory device **200**, including an array **202** of spin valve memory (SVM) cells, at least one reference SVM (RSVM) cell **204**, and a feedback controlled temperature controller **206**. The thermal-assisted magnetic memory device **200** may further include a power source **208** and a sampling circuit **210**, such as a self-reference triple sample sense circuit providing a digital output representing the state of a selected resistive device within the array **202**. A write current generator **218** may also be provided.

30

[0031] Coupled to the RSVM cell **204** is a temperature sensor **212**. The temperature sensor **212** is thermally coupled to the RSVM cell **204**, and in at least one embodiment, is physically coupled to the RSVM cell **204**. The feedback controlled temperature controller

206 receives feedback in the form of a voltage feedback from the temperature sensor **212**. The feedback is generated when power is applied by power path **214** to the RSVM cell **204** and a selected SVM cell within the array **202** to heat the RSVM cell **204** and selected array SVM cell.

5 **[0032]** The power path **214** providing the heating power to the RSVM cell **204** and to the array **202** are substantially the same. Conceptually this is shown as a single power path **214** that is branched to paths **214'** and **214''**. As such, varying the power provided to power path **214** directly results in substantially equal and symmetric variation in the power provided by paths **214'** and **214''**.

10 **[0033]** Moreover, adjusting the power delivered to RSVM cell **204** results in a substantially symmetric adjustment of power delivered to the array **202**. In other words, substantially contemporaneously with the application and adjustment of power to the RSVM cell **204**, a power is applied and adjusted to a selected array SVM cell. In at least one embodiment, the power supplied to the selected SVM cell is substantially the identical to the
15 power supplied to the RSVM cell **204**. For conceptual simplicity, the RSVM cell **204** has been illustrated as separated from the array **202**, however in at least one embodiment the RSVM cell **204** may be located within the array **202**.

[0034] FIG. 3 illustrates a perspective view of a portion of the array **202** and RSVM cell **204**. As shown, in at least one embodiment, the array **202** is a resistive cross-point memory array (CPA) **300**, comprised of spin valve memory (SVM) cells **302**, **302'**, **302''**,
20 etc. Each SVM cell **302** of the cross-point array **300** includes at least one ferromagnetic data layer **304** (also commonly referred to as a sense layer), an intermediate layer **306**, and a ferromagnetic reference layer **308**.

[0035] The ferromagnetic data layer **304** permits the storing of a bit of data as an alterable orientation of magnetization M1, and consists of a material wherein the coercivity
25 is decreased upon an increase in temperature. The intermediate layer **306** has opposing sides such that the data layer **304** in contact with one side is substantially in direct alignment with, and substantially uniformly spaced from, the reference layer **308**.

[0036] In at least one embodiment, the reference layer **308** is a pinned reference layer, characterized by a pinned orientation of magnetization M2. In at least one alternative
30 embodiment, the reference layer is a soft-reference layer, characterized by a non-pinned orientation of magnetization M2. A soft-reference layer may also have a lower coercivity than the data layer **304**.

[0037] The thermal properties of RSVM cell **204** relate to the thermal properties of the SVM cells of the array **202**, such that by observing the thermal behavior of RSVM cell **204**, the thermal behavior of the SVM cells of the array **202** may be inferred. Under appropriate circumstances RSVM cell **204** may be larger or smaller than the cells of the SVM array **202**.
5 When RSVM cell **204** is larger or smaller than the SVM cells of array **202**, and, or is not substantially proximate to array **202** it is understood and appreciated that the power applied to RSVM cell **204** corresponds to an adjusted power applied to a selected cell within the array **202**.

[0038] In at least one embodiment, the RSVM cell **204** is substantially similar to the SVM cells **302**, **302'**, **302''**, etc. of the cross-point array **300**. More specifically, in at least one embodiment the RSVM cell **204** is of substantially the same shape, size and composition as SVM cell **302**, having at least one ferromagnetic data layer **310**, an intermediate layer **312**, and a ferromagnetic reference layer **314**, arranged as described with respect to SVM cell **302**. Moreover, in at least one embodiment the RSVM cell **204** is
10 substantially identical to the SVM cells **302**, **302'**, **302''**, etc. of the cross-point array **300**. The use of a substantially identical cell advantageously simplifies the manufacturing and control process.

[0039] The ferromagnetic data layers (**304**, **310**) and the reference layers (**308**, **314**) may be made from a material that includes, but is not limited to: Nickel Iron (NiFe), Nickel Iron Cobalt (NiFeCo), Cobalt Iron (CoFe), and alloys of such metals. More specifically, in
20 at least one embodiment the data layers (**304**, **310**) and the reference layers (**308**, **314**) are Nickel Iron (NiFe). In addition, both the data layers (**304**, **310**) and the reference layers (**308**, **314**) may be formed from multiple layers of materials. However, for conceptual simplicity and ease of discussion, each layer component is herein discussed as a single layer.

[0040] As shown, a plurality of electrically conductive columns **316**, **316'** and **316''** cross a plurality of electrically conductive rows **318**, **318'** and **318''**, thereby forming a plurality of intersections. Each SVM cell **302**, **302'**, **302''**, etc. of the cross-point array **300** is in electrical contact with and located at an intersection between a row and column. As such, electrical current and magnetic fields may be provided to a selected SVM cell **302**
25 within the cross-point array **300** by electrically conductive column **316** and electrically conductive row **318**.
30

[0041] Likewise, RSVM cell **204** has a top electrical conductor **320** and a bottom electrical conductor **322**. In addition, RSVM cell **204** is thermally coupled to a temperature sensor **324**, such as a PN junction diode.

5 [0042] In at least one embodiment, the SVM cells of the cross-point array **300** and the RSVM cell **204** self-heat. More specifically, power flowing through a given SVM cell **302** as provided by column **316** and row **318**, and power flowing through the RSVM cell **204** as provided by top electrical conductor **320** and bottom electrical conductor **322**, will encounter resistance in the tunneling action of the current through the cell and result in a significant and localized rise in temperature within the SVM cell **302** and RSVM cell **204**.
10 The power applied may be a heating pulse of about 1 to 3 volts.

[0043] In at least one alternative embodiment, the SVM cells **302**, **302'**, **302''**, etc. of the cross-point array **300** and the RSVM cell **204** are heated by coupled heating. More specifically, heating power flows through a separate heating device, such as movable nano-tip probe **350** that thermally couples to selected cross-point array SVM cell **302**. A
15 substantially identical separate heating device, such as nano-tip probe **350'** is also provided to thermally couple to the RSVM cell **204**. In at least one embodiment, the nano-tip probe **350** has an articulating support **352**, a distal tip **354** and a heat conductor **356**.

[0044] The nano-tip probe **350'** thermally coupling to the RSVM cell **204** is substantially similar, having an articulating support **352'**, a distal tip **354'** and a heat
20 conductor **356'**. Under appropriate circumstances, such as where the SVM cells of array **202** share a common bottom conductor, the nano-tip probe **350** may also provide an appropriate top electrical conductor.

[0045] Nano-tip probe **350** is movable and as such can be moved from a location proximate to one SVM cell **302** to a location proximate to another SVM cell, such as SVM
25 cell **302'**. Specifically, the probe may be positioned along the X and Y coordinate axis above a given SVM cell **302**. The probe may then be positioned along the Z coordinate axis to permit the transfer of power (heat and or electrical current) between the nano-tip probe **350** and the selected SVM cell **302**.

[0046] FIG. 4 provides a conceptual electrical schematic of the thermal-assisted magnetic memory device **200**, characterized by an array **202**, an RSVM cell **204**, and a
30 feedback controlled temperature controller **206**. To assist with discussion, specific elements of this schematic have been set apart by dotted boxes, specifically, the RSVM cell heater **400**, the thermal circuit **402** of RSVM cell **204**, the temperature sensor **404**, the temperature

controller **406**, and the power source **408**. In at least one embodiment, power source **408** is a current mirror.

5 **[0047]** In this conceptual electrical schematic, the RSVM cell **204** is depicted as a resistive element, **410**. As power is provided by conductive line **412** to resistive element **410** (RSVM cell **204**), internal resistance results in generation of heat energy, represented as P_H , represented by curved arrow **414**. The thermal circuit **402** is coupled to the RSVM cell heater **400**. More specifically, the power dissipated in resistive element **410** results in a power source for the thermal circuit, as the structure of the circuit determines the thermal resistance and temperature rise as a matter of thermal resistances.

10 **[0048]** The heat P_H serves as a power source **416** in thermal circuit **402**. The thermal resistance (R_T) of the RSVM cell **204** to a temperature sensing diode in the silicon substrate is represented by resistor **418**. The thermal resistance of the temperature sensing diode to the ambient temperature is represented by resistor **420**.

15 **[0049]** The current flowing through resistors **418** and **420** couples the temperature to the PN junction diode **422** by connection **424**. The behavior of the PN junction diode **422** is well understood to respond to temperature, on the order of 2 to 4 micro volts per degree centigrade. The junction voltage developed by the diode current (I_D) flowing through the PN junction diode **422**, is provided as feedback (V_T) to the negative input of a negative feedback differential amplifier **426**.

20 **[0050]** The function of the negative feedback differential amplifier **426** is to reduce the differences between two input voltages. A reference voltage, V_{ref} , is applied to the "+" terminal and the feedback voltage V_T is applied to the "-" terminal. The reference voltage, V_{ref} , represents a specific temperature. In at least one embodiment, V_{ref} represents the temperature for a reduced coercivity of the RSVM cell (i.e., RSVM cell **204**). Under
25 appropriate circumstances, V_{ref} may represent operating temperatures desired for a specific application of the thermal-assisted magnetic memory device **200**.

30 **[0051]** The negative feedback differential amplifier **426** reduces the difference between the two input voltages, V_{ref} and V_T , by directing an adjustment to the power source **408**. In at least one embodiment, the power source **408** is a varying current source **428**, providing substantially the same power to resistive element **410** and a selected SVM cell **302**, represented as resistive element **430**, within array **202**, illustrated as cross-point array **300**. An increase or decrease in the current (power), provided to the RSVM cell by conductor **412**, represented as dotted line **432**, is substantially the same as the current (power) provided

to resistive element **430** (selected SVM cell **302**) of the cross-point array **300**. Selected by row select element **434** and column select element **436**, the path of the current supplied to resistive element **430** is represented by dotted line **438**.

5 **[0052]** The operation of the thermal-assisted magnetic memory device **200**, as conceptually illustrated in FIG. 4, may be summarized as follows: A substantially equal heat power is applied to resistive element **410** and resistive element **430**. The heat power dissipated in the resistive element **410** is coupled to a thermal circuit **402**. The temperature rise in resistive element **410** above the ambient temperature is recognized and represented by the thermal circuit **402**.

10 **[0053]** The thermal circuit **402** is coupled to an electrical circuit at PN junction diode **422**. A sense current is passed through the PN junction diode. The voltage developed by the PN junction diode, V_T , is compared to a reference voltage, V_{ref} , by negative feedback differential amplifier **426**. Based upon negative feedback, the heat power is adjusted to regulate the feedback voltage V_T , to be substantially equal to the reference voltage, V_{ref} .
15 By regulating the power to equalize the voltages, the temperature of the resistive element **410** will be substantially identical to the temperature of the selected resistive element **430**.

20 **[0054]** It is appreciated that the ambient temperature of the RSVM cell **204** is substantially about the same as the ambient temperature of the SVM cells in the array **202**. Moreover, the heating behavior illustrated in RSVM cell heater **400** is substantially the same for a resistive element **430** (selected SVM cell **302**) within the array **202**. Although the RSVM cell heater **400** is illustrated as a function of the applied power being a varying current, it is to be understood and appreciated that the power may be an applied voltage, a high frequency (RF) power, laser or other form of power sufficient to provide a localized source of heat.

25 **[0055]** The thermal-assisted magnetic memory device **200** with feedback controlled temperature controller **206** advantageously permits reliable thermal-assisted write operations depending on elevated temperatures of the selected SVM cells. Such thermal-assisted operations are controlled to a very narrow and precise temperature range. Moreover, variations in ambient temperature (i.e., the substrate temperature) affecting the final
30 temperature of the array SVM cells is effectively eliminated. This elimination is advantageously accomplished without requiring each SVM cell of the array **202** to be fitted with an individual temperature sensor.

[0056] Having described the above physical embodiment of the thermal-assisted magnetic memory device **200** with RSVM cell **204** and feedback controlled temperature controller **206**, another embodiment relating to the method of use will now be described with reference to the Flowchart of FIG. 5 and the components illustrated in FIGS. 2, 3 and 4. It will be appreciated that the described method need not be performed in the order in which it is herein described, but that this description is merely exemplary of at least one method for using the controlled temperature, thermal-assisted magnetic memory device **200**, in accordance with the present invention.

[0057] Referring to the components illustrated in FIGS. 3 and 4, and as indicated in the Flowchart of FIG. 5, the selection of a specific SVM cell is made, block **500**. Such a selection may be performed with the use of row select element **434** and column select element **436** selecting a specific column **316** and specific row **318** to select a specific SVM cell **302**.

[0058] A first power is applied to RSVM cell **204**. The first power is a heating power and the application serves to heat the RSVM cell **204**, block **502**. A second power, substantially identical to the first power, is applied to the selected resistive element **430** (selected SVM cell **302**), block **504**.

[0059] In at least one embodiment the application of the first and second powers results in self-heating within the RSVM cell **204** and selected resistive element **430**. In an alternative embodiment, the heating is achieved by coupled heating, wherein the first and second powers are applied to separate heating devices that are thermally coupled to RSVM cell **204** and selected resistive element **430**.

[0060] It is generally appreciated in the magnetic memory arts that as the size of a magnetic bit decreases, the coercivity of the bit will increase. For example, a 0.25 x 0.75 micrometer bit may have a coercivity of about 40 Oe [1 Oe = 1000/(4*pi) A/m], whereas a 0.15 x 0.45 micrometer bit may have a coercivity of about 75 Oe [1 Oe = 1000/(4*pi) A/m]. In general, the coercivity of a material will decrease as temperature increases. For example a 100 degrees Celsius rise in temperature may impart a drop in coercivity of about 50%. Upon a decrease in temperature to the original state, the original coercivity will generally return.

[0061] As such, applying a heating power to the RSVM cell **204** will reduce the coercivity of RSVM cell **204**. As RSVM cell **204** is substantially identical to the SVM cells of the array **202**, by measuring and controlling the temperature of resistive element **410**

(RSVM cell **204**), it is possible to infer substantially the same control of temperature applied to the selected resistive element **430** (selected SVM cell **302**).

5 **[0062]** To permit this control of temperature, a feedback voltage V_T , is sensed from the temperature controller **206** coupled to the RSVM cell **204**, block **506**. The feedback voltage V_T is compared to reference voltage V_{ref} , block **510**. The reference voltage, V_{ref} , represents a specific temperature, and in at least one embodiment represents the reduced coercivity of RSVM cell **204** and selected SVM cell **302**.

10 **[0063]** Based upon the comparison of V_T to V_{ref} , the negative feedback differential amplifier **426** adjusts the variable first power applied to the RSVM cell **204**, block **512**. As the power is supplied by power source **408**, the second power applied to the resistive element **430** is likewise adjusted to be substantially identical to the first power, block **514**.

15 **[0064]** With the desired temperature achieved in the RSVM cell **204** and, by implication, in the selected SVM cell **302**, a write magnetic field is applied to the selected SVM cell **302**, block **516**. The magnetic field applied is greater than the reduced coercivity of the selected SVM cell **302**. As the coercivity of the resistive element **430** (selected SVM cell **302**) has been reduced by the application of power in the form of heat, the orientation of magnetization of the selected SVM cell **302** may be changed. Appropriate sensing operations may be combined with the write operation to confirm the write operation has succeeded.

20 **[0065]** As indicated in decision operation **518**, additional write operations repeat the above described method. This method advantageously permits accurate thermal-assist write operations to be performed. As such, the margins of buffering space between SVM cells within the array **202** may be reduced.

25 **[0066]** Another embodiment may be appreciated to be a computer system incorporating the thermal-assisted magnetic memory device **200**. A computer with a main board, at least one CPU and the thermal-assisted magnetic memory device **200**, as described above with reference to FIG. 4, raises the advantages of the improved thermal-assisted magnetic memory device **200** to a system level.

30 **[0067]** While the invention has been described with reference to the preferred embodiment, it will be understood by those skilled in the art that various alterations, changes and improvements may be made and equivalents may be substituted for the elements thereof and steps thereof without departing from the scope of the present

invention. In addition, many modifications may be made to adapt to a particular situation or material to the teachings of the invention without departing from the essential scope thereof. Such alterations, changes, modifications, and improvements, though not expressly described above, are nevertheless intended and implied to be within the scope and spirit of the invention. Therefore, it is intended that the invention not be limited to the particular embodiments disclosed as the best mode contemplated for carrying out this invention, but that the invention will include all embodiments falling within the scope of the appended claims.